



SANYO Semiconductors

DATA SHEET

2SK4181 — N-Channel Silicon MOSFET

General-Purpose Switching Device

Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Avalanche resistance guarantee.
- For use of lighting & etc.
- High-density mounting.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		525	V
Gate-to-Source Voltage	V_{GSS}		± 30	V
Drain Current (DC)	I_D		7.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	30	A
Allowable Power Dissipation	P_D	$T_c=25^\circ\text{C}$ (SANYO's ideal heat dissipation condition*1)	70	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single pulse) *2	E_{AS}		34	mJ
Avalanche Current *3	I_{AV}		7.5	A

*1 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*2 $V_{DD}=99\text{V}$, $L=1\text{mH}$, $I_{AV}=7.5\text{A}$

*3 $L \leq 1\text{mH}$, single pulse

Marking : K4181

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

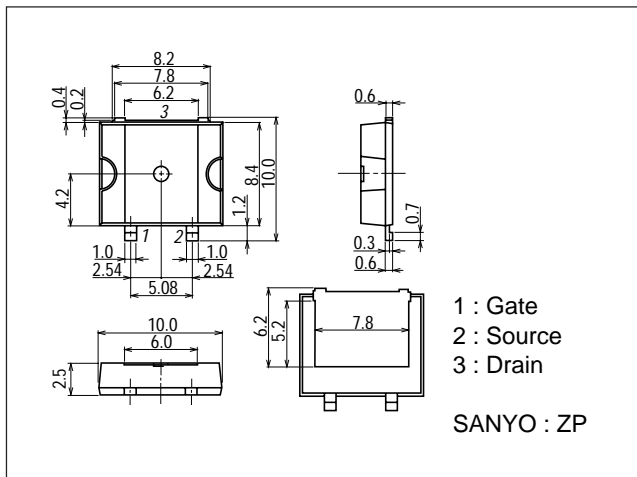
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =10mA, V _{GS} =0V	525			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =420V, V _{GS} =0V			100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =3.7A	1.9	3.8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)}	I _D =3.7A, V _{GS} =10V		0.71	0.92	Ω
Input Capacitance	C _{iss}	V _{DS} =30V, f=1MHz		600		pF
Output Capacitance	C _{oss}	V _{DS} =30V, f=1MHz		125		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =30V, f=1MHz		27		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		20		ns
Rise Time	t _r	See specified Test Circuit.		60		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		77		ns
Fall Time	t _f	See specified Test Circuit.		38		ns
Total Gate Charge	Q _g	V _{DS} =200V, V _{GS} =10V, I _D =7.5A		24		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =200V, V _{GS} =10V, I _D =7.5A		4.5		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =200V, V _{GS} =10V, I _D =7.5A		13.8		nC
Diode Forward Voltage	V _{SD}	I _S =7.5A, V _{GS} =0V		0.9	1.2	V

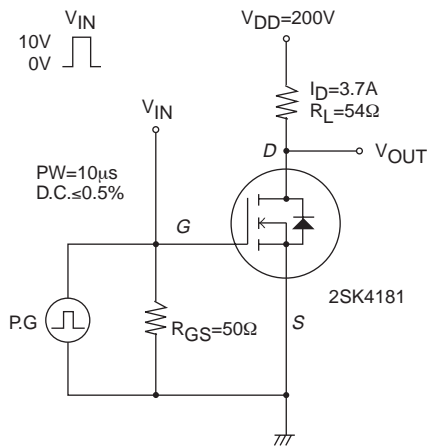
Package Dimensions

unit : mm (typ)

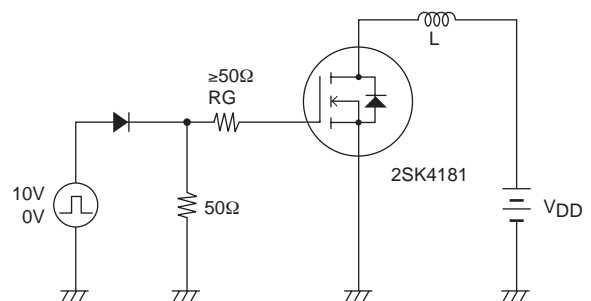
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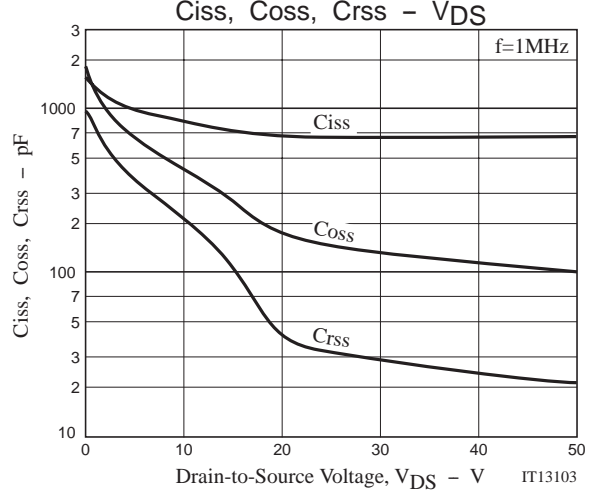
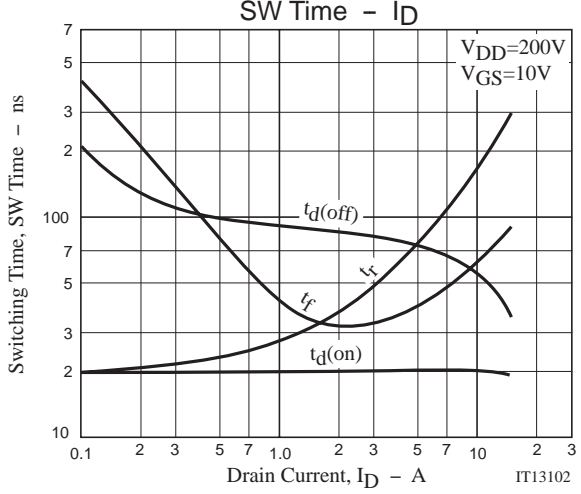
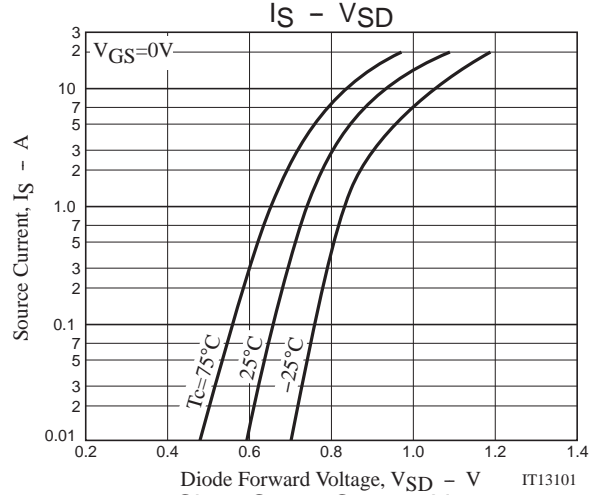
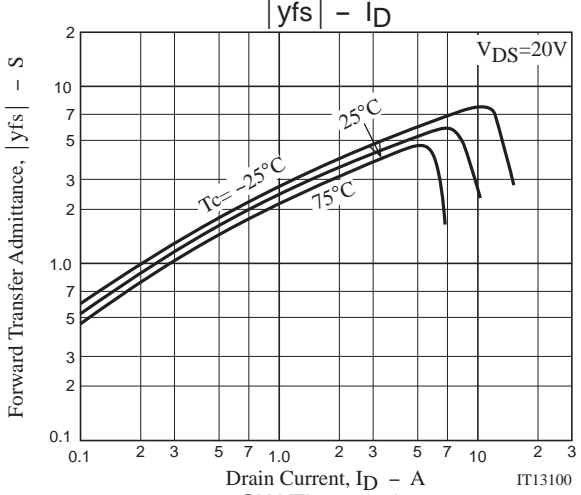
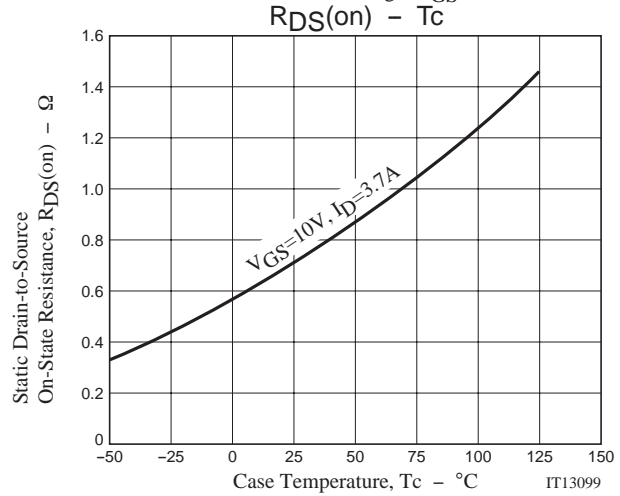
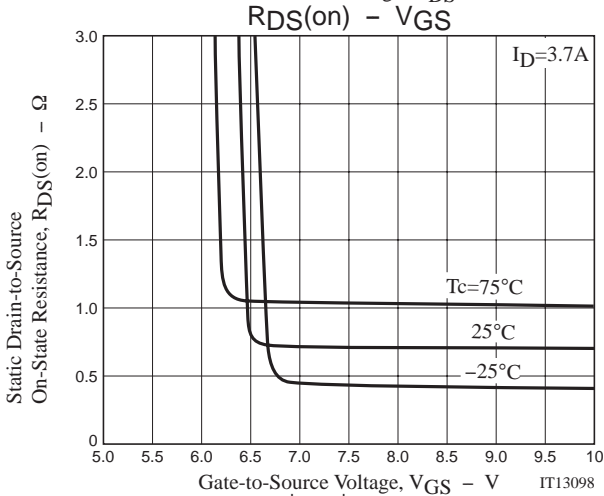
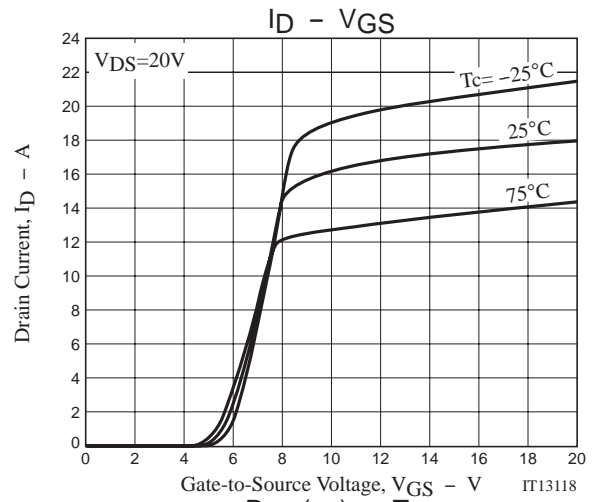
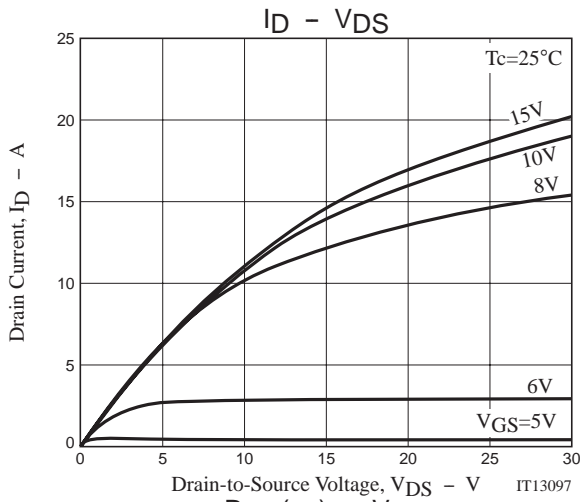


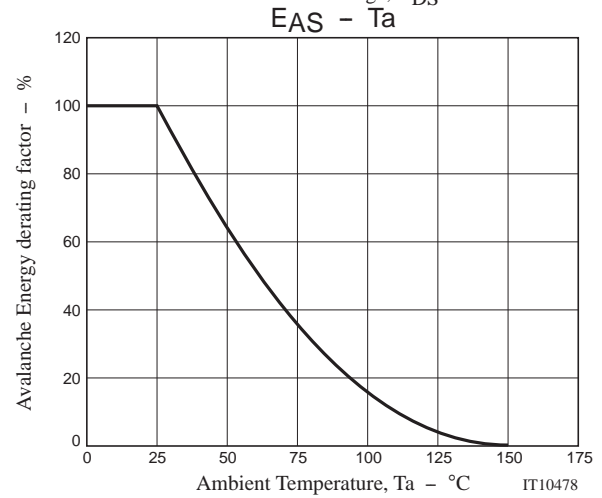
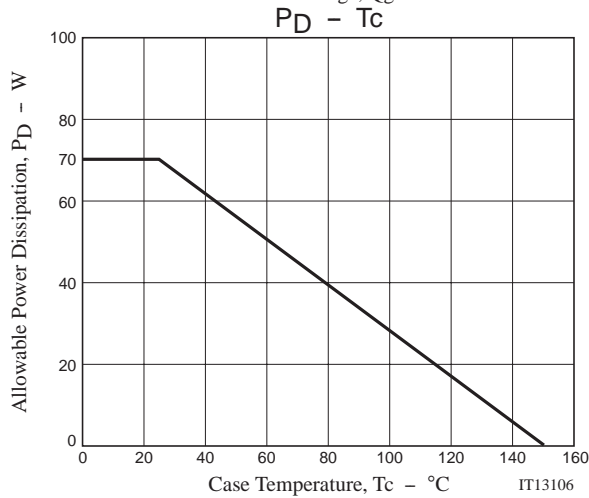
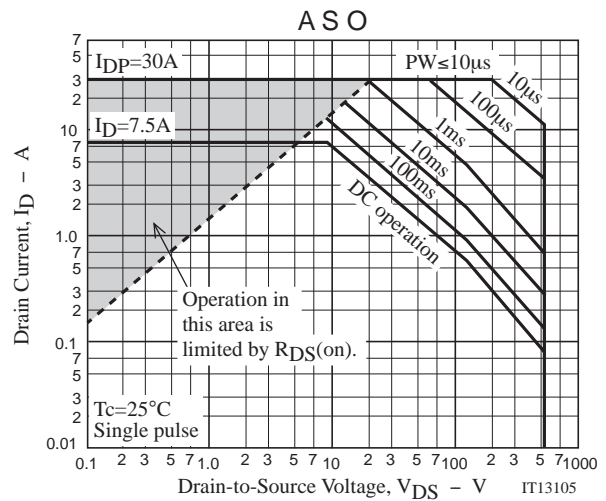
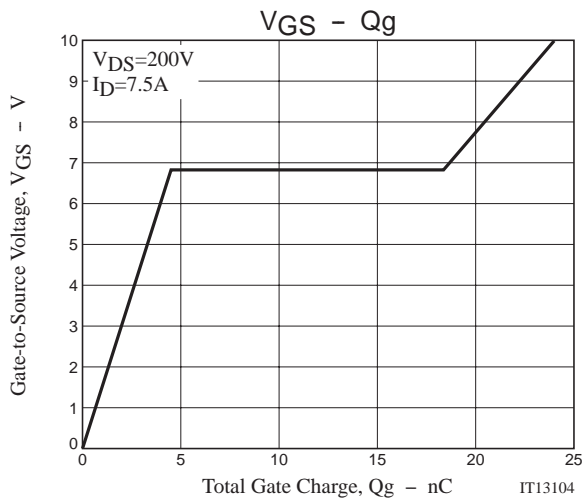
Switching Time Test Circuit



Avalanche Resistance Test Circuit







Note on usage : Since the 2SK4181 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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